

Relaxation of electrical properties of epitaxial $\text{Cd}_x\text{Hg}_{1-x}\text{Te}$: As(Sb) layers converted into n -type by ion milling

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Results on the studies of the relaxation of electrical properties of As- and Sb-doped HgCdTe epitaxial layers, which were converted into n -type by ion milling (IM), are presented. It is demonstrated that donor complexes formed under IM, are not stable, and their concentration decreases upon storage even at the room temperature. It was found that the process responsible for the relaxation was disintegration of the complexes that started after the end of the IM and was caused by the decrease in concentration of interstitial mercury atoms, generated by IM.

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Статья поступила в редакцию 11 октября 2006 г.